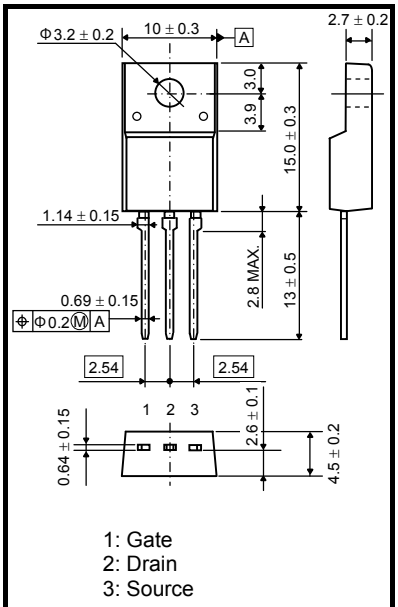
TK12A60D

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 0.45 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 7.5 S (typ.)
- Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 600 V)
- Enhancement-mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	SC-67
TOSHIBA	2-10U1B

Weight : 1.7 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

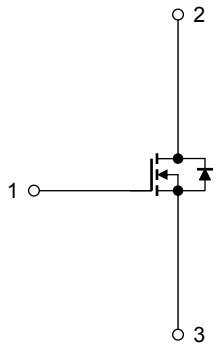
Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	I_D	12	A
	Pulse (Note 1)	I_{DP}	48	
Drain power dissipation (Tc = 25°C)		P_D	45	W
Single pulse avalanche energy (Note 2)		E_{AS}	359	mJ
Avalanche current		I_{AR}	12	A
Repetitive avalanche energy (Note 3)		E_{AR}	4.5	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch-c)}$	2.78	°C/W
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	62.5	°C/W

Internal Connection



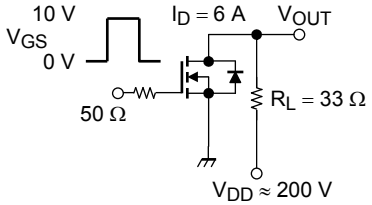
Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 4.36 mH, R_G = 25 Ω, I_{AR} = 12 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	—	—	±1	μA
Drain cut-off current		I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	600	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 6 A	—	0.45	0.55	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 6 A	1.9	7.5	—	S
Input capacitance		C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	—	1800	—	pF
Reverse transfer capacitance		C_{rss}		—	9	—	
Output capacitance		C_{oss}		—	190	—	
Switching time	Rise time	t_r	 Duty ≤ 1%, t_w = 10 μs	—	40	—	ns
	Turn-on time	t_{on}		—	80	—	
	Fall time	t_f		—	15	—	
	Turn-off time	t_{off}		—	110	—	
Total gate charge		Q_g	V_{DD} ≈ 400 V, V_{GS} = 10 V, I_D = 12 A	—	38	—	nC
Gate-source charge		Q_{gs}		—	24	—	
Gate-drain charge		Q_{gd}		—	14	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	12	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	48	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 12 A, V_{GS} = 0 V	—	—	−1.7	V
Reverse recovery time	t_{rr}	I_{DR} = 12 A, V_{GS} = 0 V, dI_{DR}/dt = 100 A/μs	—	1200	—	ns
Reverse recovery charge	Q_{rr}		—	13	—	μC

Marking